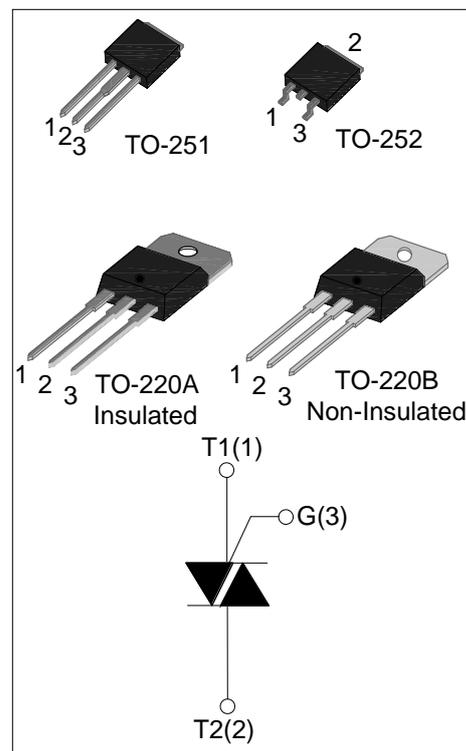




### DESCRIPTION:

JST06 series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interference. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

JST06A provides insulation voltage rated at 2500V RMS from all three terminals to external heatsink complying with UL standards (File ref: E252906).



### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	6	A
$V_{DRM}/V_{RRM}$	600 and 800	V

### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40 - 150	°C
Operating junction temperature range		$T_j$	-40 - 125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	600/800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	600/800	V
Non repetitive surge peak Off-state voltage		$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	TO-251/ TO-252 TO-220B(Non-Ins) ( $T_C=107^\circ\text{C}$ )	$I_{T(RMS)}$	6	A
	TO-220A(Ins) ( $T_C=100^\circ\text{C}$ )			
Non repetitive surge peak on-state current (full cycle, F=50Hz)		$I_{TSM}$	60	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	18	$\text{A}^2\text{s}$

Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )	dI/dt	50	A/ $\mu$ s
Peak gate current	$I_{GM}$	2	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	5	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value				Unit
				TW	SW	CW	BW	
$I_{GT}$	$V_D=12\text{V } R_L=30\Omega$	I - II -III	MAX	5	10	35	50	mA
$V_{GT}$		I - II -III	MAX	1.5				V
$V_{GD}$	$V_D=V_{DRM} T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II -III	MIN	0.2				V
$I_L$	$I_G=1.2I_{GT}$	I - III	MAX	10	15	50	70	mA
		II		15	25	60	80	
$I_H$	$I_{TM}=0.2\text{A}$		MAX	6	10	35	60	mA
dV/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^\circ\text{C}$		MIN	20	50	400	1000	V/ $\mu$ s

**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=8.5\text{A } t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.55	V
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	1	mA

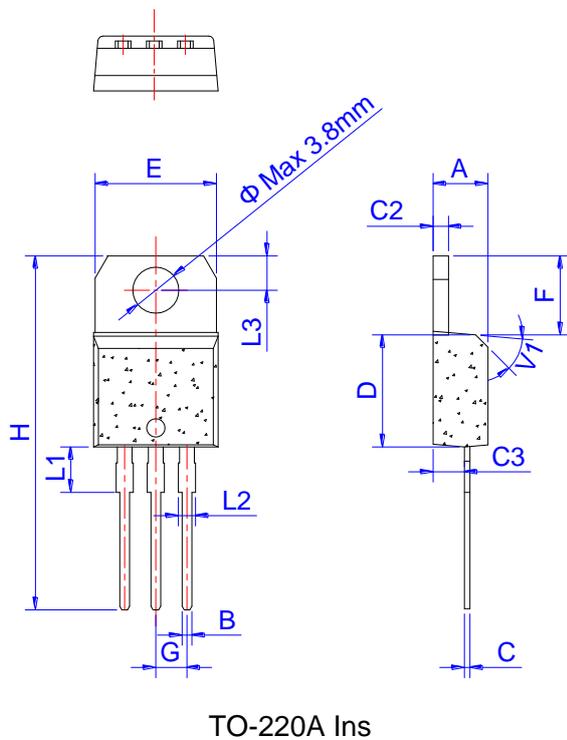
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-251/ TO-252	3.5	$^\circ\text{C/W}$
		TO-220A(Ins)	3.9	
		TO-220B(Non-Ins)	2.4	

ORDERING INFORMATION

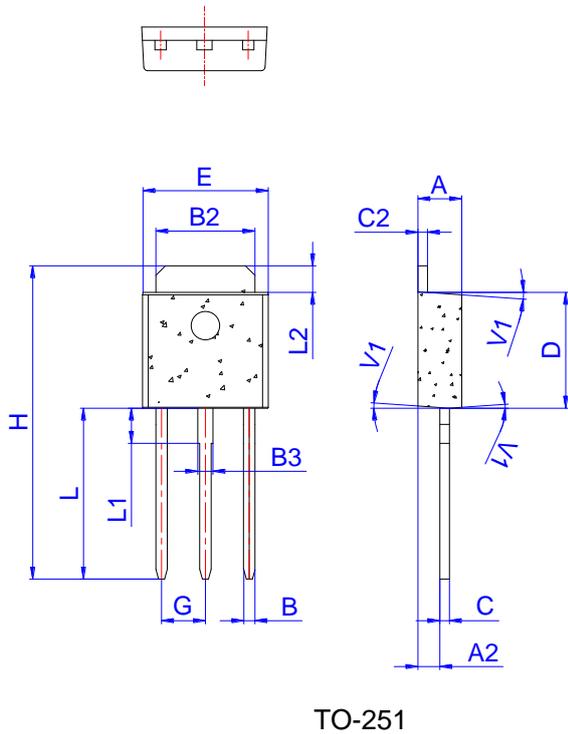
J	ST	06	B	-600	TW
JieJie Microelectronics Co.,Ltd	Triacs	I <sub>T(RMS)</sub> :6A H:TO-251 K:TO-252 A:TO-220A(Ins) B:TO-220B(Non-Ins)			TW: I <sub>GT1-3</sub> ≤5mA SW: I <sub>GT1-3</sub> ≤10mA CW: I <sub>GT1-3</sub> ≤35mA BW: I <sub>GT1-3</sub> ≤50mA  600: V <sub>DRM</sub> /V <sub>RRM</sub> ≥600V 800: V <sub>DRM</sub> /V <sub>RRM</sub> ≥800V

PACKAGE MECHANICAL DATA

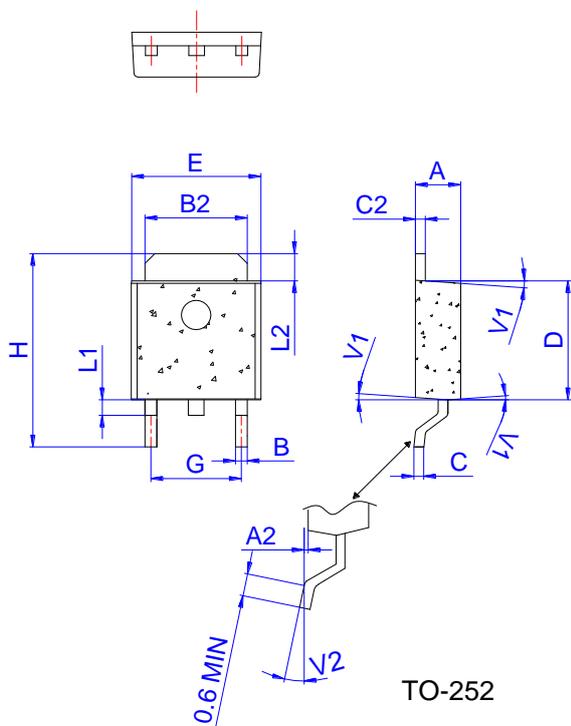


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

PACKAGE MECHANICAL DATA

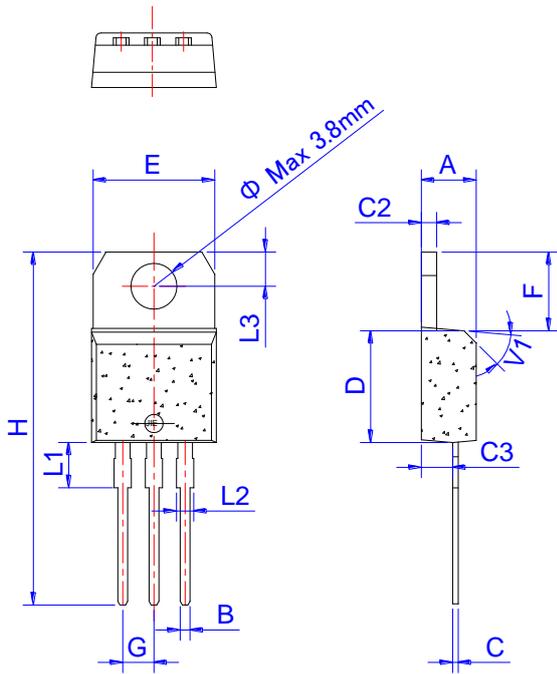


Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.90		1.20	0.035		0.047
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
B3	0.76		0.85	0.030		0.033
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G		2.30			0.091	
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		1.90	0.071		0.075
L2	1.37		1.50	0.054		0.059
V1		4°			4°	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	0.03		0.23	0.001		0.009
B	0.55		0.65	0.022		0.026
B2	5.10		5.40	0.200		0.213
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	4.40		4.70	0.173		0.185
H	9.35		10.6	0.368		0.417
L1	1.30		1.70	0.051		0.067
L2	1.37		1.50	0.054		0.059
V1		4°			4°	
V2	0°		8°	0°		8°

PACKAGE MECHANICAL DATA



TO-220B Non-Ins

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.60		10.4	0.378		0.409
F	6.20		6.60	0.244		0.260
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

FIG.1 Maximum power dissipation versus RMS on-state current

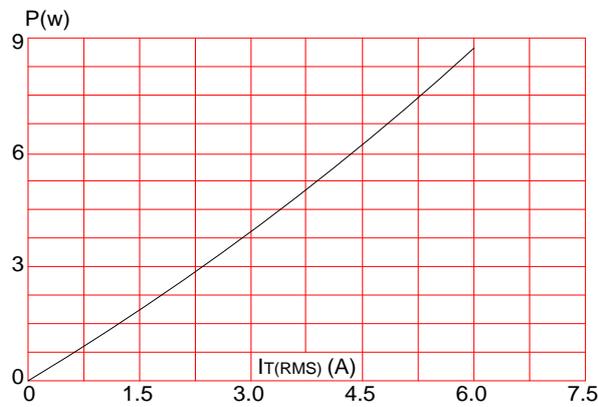
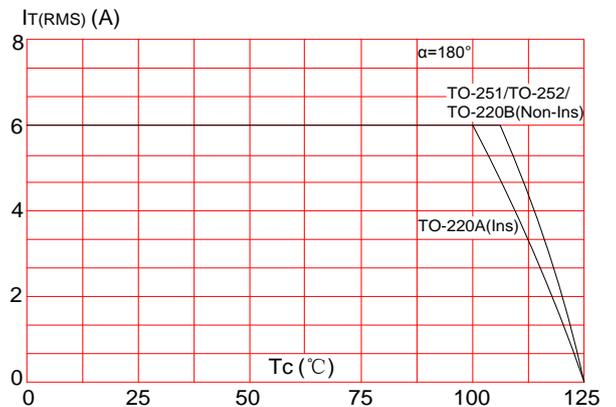
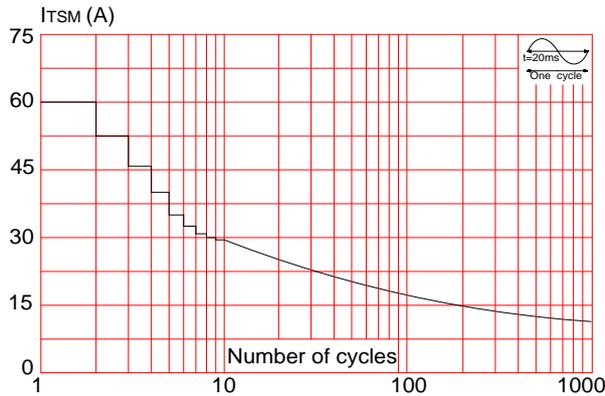


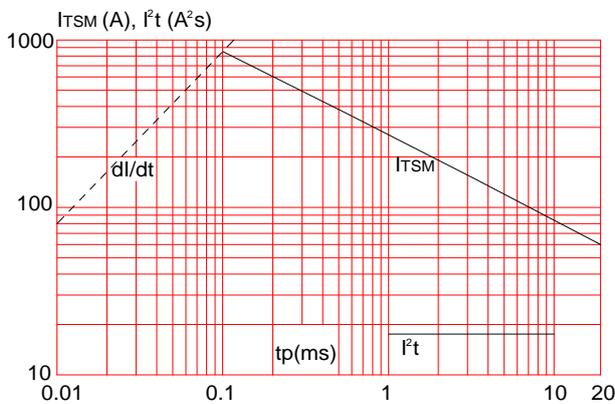
FIG.2: RMS on-state current versus case temperature



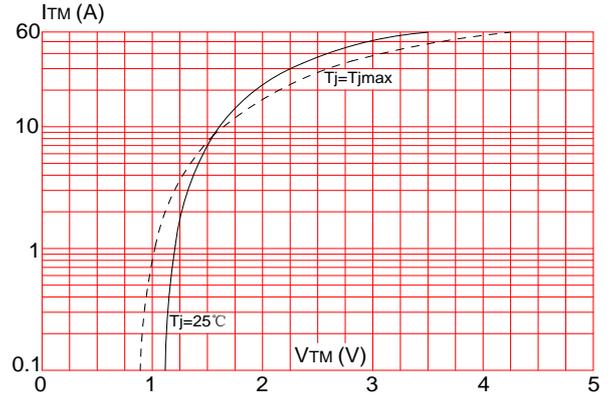
**FIG.3:** Surge peak on-state current versus number of cycles



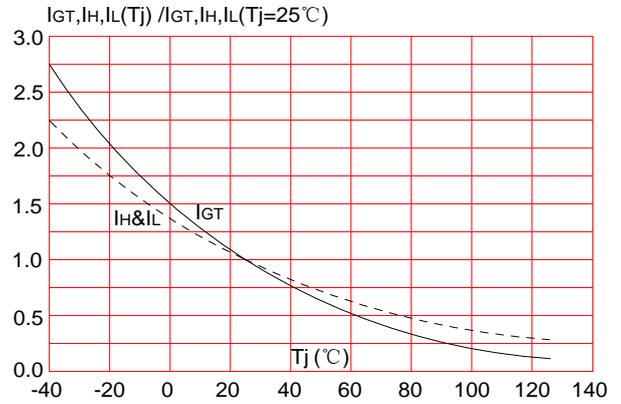
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 50\text{A}/\mu\text{s}$ )



**FIG.4:** On-state characteristics (maximum values)



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



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